Sub	stitute for form 1449/PTO			Complete if Known		
				Application Number	10/774,890-Conf. #8754	
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s	TATEMENT E	3Y /	APPLICANT	First Named Inventor	Eugene A. Fitzgerald	
				Art Unit	2818	
(Use as many sheets as necessary)			necessary)	Examiner Name	D. A. Le	
Sheet	1	of	2	Attorney Docket Number	ASC-049C1	

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	NON PATENT LITERATURE DOCUMENTS						
Examiner Initials	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>				
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considered. Include copy of this form with next communication to applicant.

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				Application Number	10/774,890-Conf. #8754	
II.	<b>IFORMATION</b>	I DI	SCLOSURE	Filing Date February 9, 2004		
s	TATEMENT E	3Y /	APPLICANT	First Named Inventor	Eugene A. Fitzgerald	
				Art Unit	2818	
(Use as many sheets as necessary)			necessary)	Examiner Name	D. A. Le	
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